

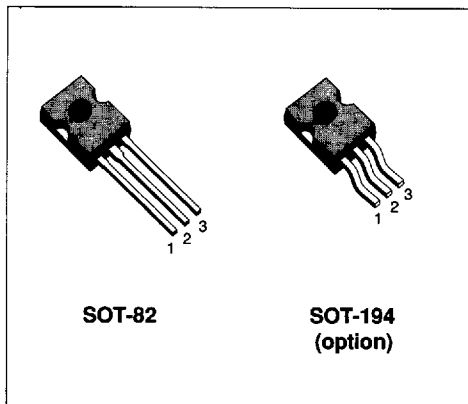
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
STK4N30L	300 V	< 1.4 Ω	4.2 A

- TYPICAL R_{DS(on)} = 1.25 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

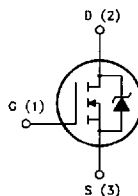
- HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- MOTOR CONTROL, AUDIO AMPLIFIERS
- INDUSTRIAL ACTUATORS
- DC-DC & DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL AND CONSUMER ENVIRONMENT
- PARTICULARLY SUITABLE FOR ELECTRONIC FLUORESCENT LAMP BALLASTS



SOT-82

SOT-194
(option)

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	300	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	300	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	4.2	A
I _D	Drain Current (continuous) at T _c = 100 °C	2.6	A
I _{DM} (*)	Drain Current (pulsed)	16	A
P _{tot}	Total Dissipation at T _c = 25 °C	60	W
	Derating Factor	0.48	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.08	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	80	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Case-sink	Typ	0.7	$^{\circ}\text{C}/\text{W}$
T_I	Maximum Lead Temperature For Soldering Purpose		275	$^{\circ}\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	4.2	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	32	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	1	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100^{\circ}\text{C}$, pulse width limited by T_j max, $\delta < 1\%$)	2.6	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ $V_{GS} = 0$	300			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125^{\circ}\text{C}$			250 1000	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\text{ }\mu\text{A}$	1	1.6	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 5\text{ V}$ $I_D = 2.5\text{ A}$ $V_{GS} = 5\text{ V}$ $I_D = 2.5\text{ A}$ $T_c = 100^{\circ}\text{C}$		1.25	1.4 1.8	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	4			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 2.5\text{ A}$	2	5		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0$		580	780	pF
C_{oss}	Output Capacitance			75	120	pF
C_{rss}	Reverse Transfer Capacitance			14	25	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 150\text{ V}$ $I_D = 2\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 5\text{ V}$ (see test circuit, figure 3)		70 165	90 215	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 240\text{ V}$ $I_D = 4\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 5\text{ V}$ (see test circuit, figure 5)		115		A/ μ s
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 240\text{ V}$ $I_D = 4\text{ A}$ $V_{GS} = 5\text{ V}$		16 5 7	22	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(off)}$	Off-voltage Rise Time	$V_{DD} = 240\text{ V}$ $I_D = 4\text{ A}$		60	80	ns
t_f	Fall Time	$R_G = 50\ \Omega$ $V_{GS} = 5\text{ V}$		50	65	ns
t_c	Cross-over Time	(see test circuit, figure 5)		120	160	ns

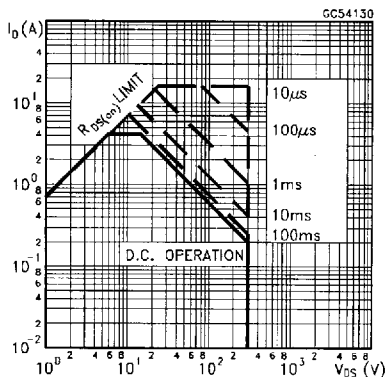
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				20	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 5\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 5\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, figure 5)		360		ns
Q_{rr}	Reverse Recovery Charge			2.4		μC
I_{RRM}	Reverse Recovery Current			13		A

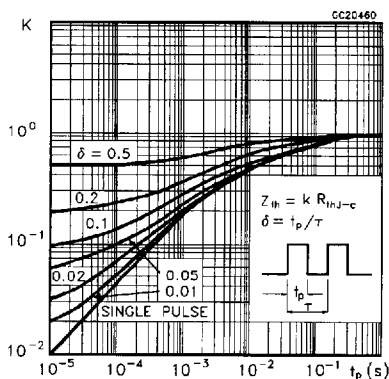
(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(*) Pulse width limited by safe operating area

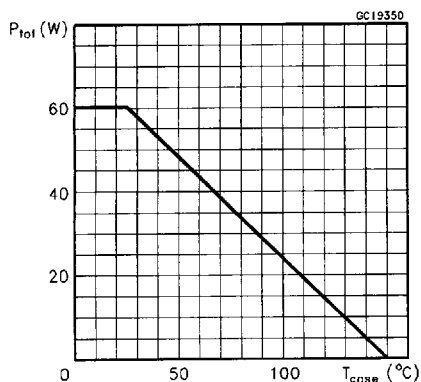
Safe Operating Area



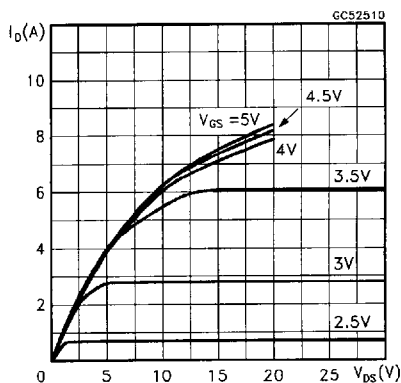
Thermal Impedance



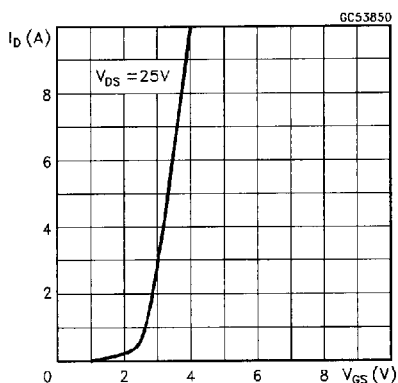
Derating Curve



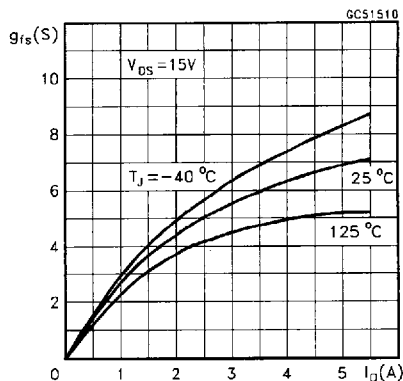
Output Characteristics



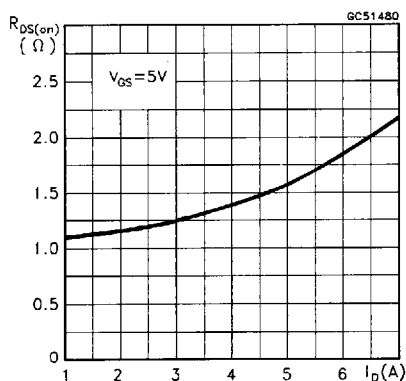
Transfer Characteristics



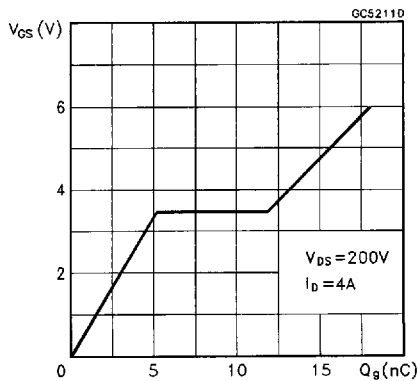
Transconductance



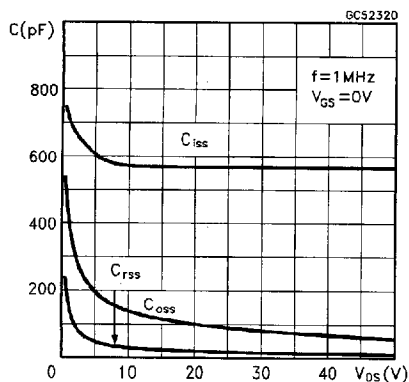
Static Drain-source On Resistance



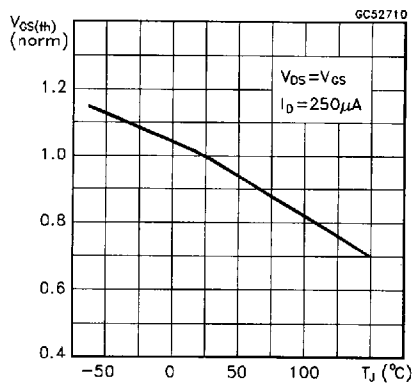
Gate Charge vs Gate-source Voltage



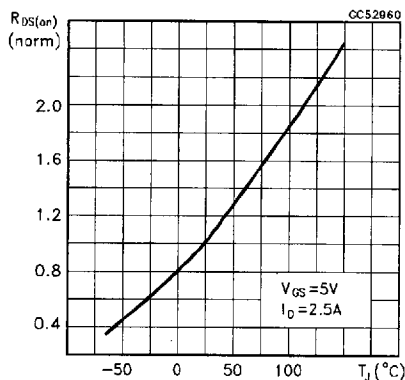
Capacitance Variations



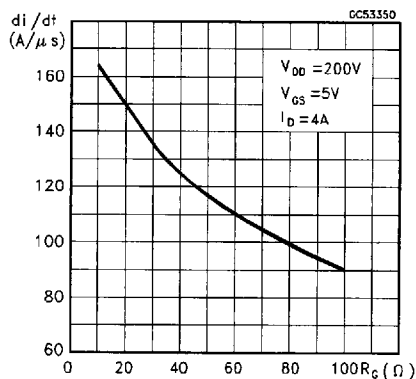
Normalized Gate Threshold Voltage vs Temperature



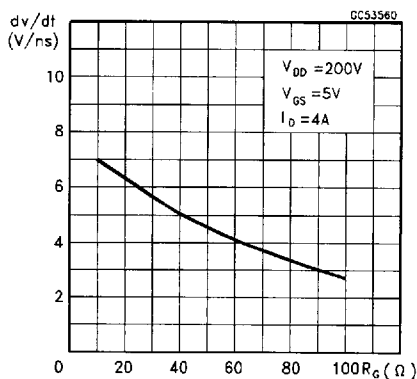
Normalized On Resistance vs Temperature



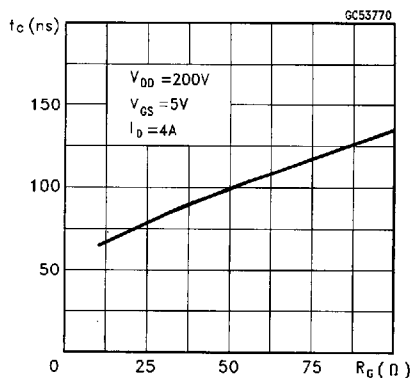
Turn-on Current Slope



Turn-off Drain-source Voltage Slope

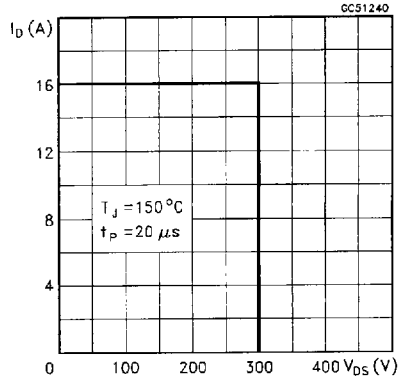
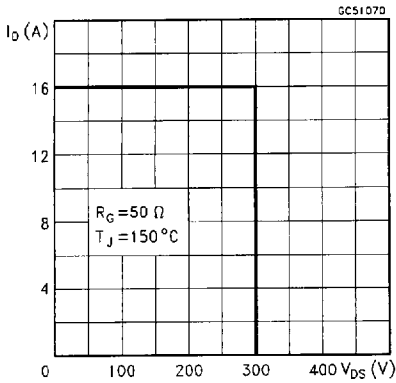


Cross-over Time



Switching Safe Operating Area

Accidental Overload Area



Source-drain Diode Forward Characteristics

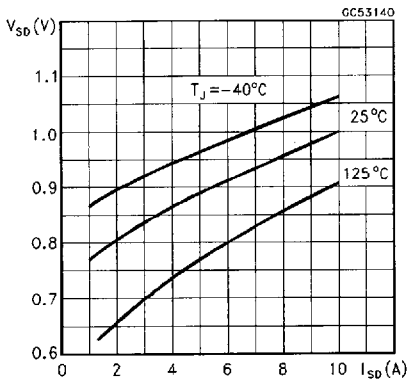


Fig. 1: Unclamped Inductive Load Test Circuits

Fig. 2: Unclamped Inductive Waveforms

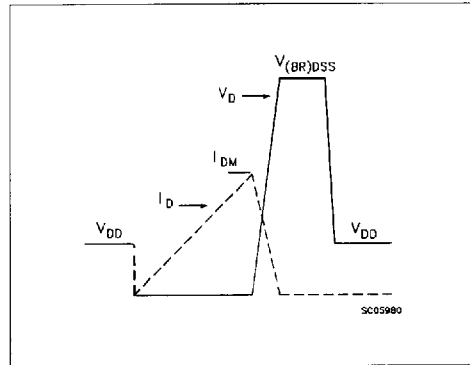
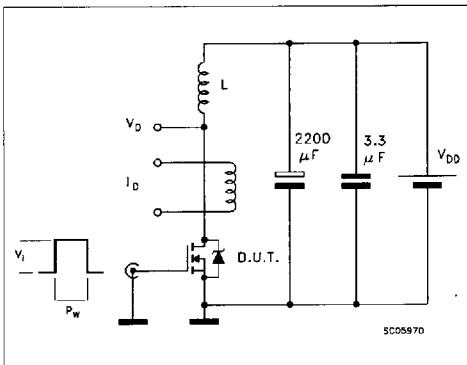


Fig. 3: Switching Times Test Circuits For Resistive Load

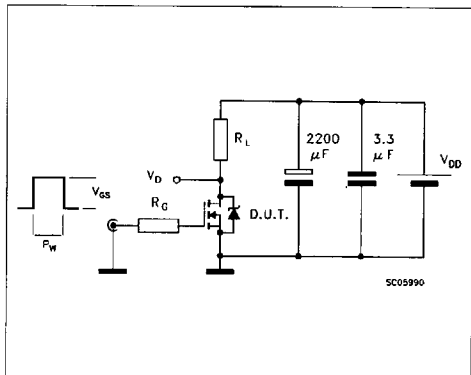


Fig. 4: Gate Charge Test Circuit

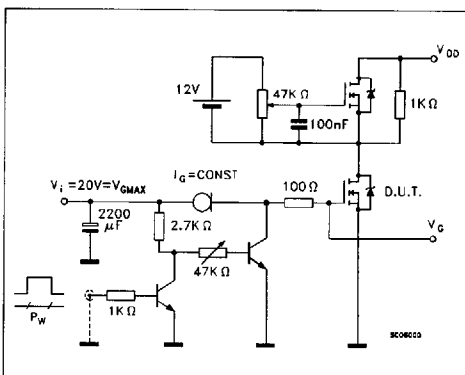


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

